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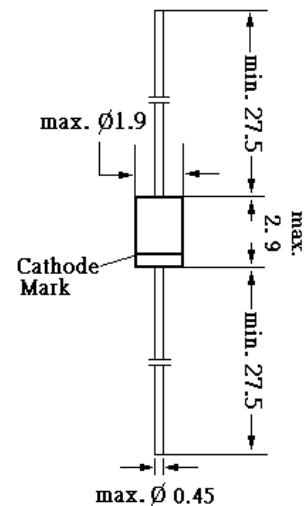
SILICON EPITAXIAL PLANAR DIODE

HIGH VOLTAGE SWITCHING

GENERAL PURPOSE RECTIFICATION APPLICATIONS

Features

- Glass sealed envelope. (MSD)
- $V_{RM} = 250V$ guaranteed.
- High reliability.



Glass case JEDEC DO-34

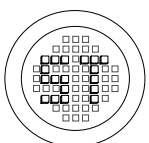
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	250	V
DC reverse voltage	V_R	220	V
Peak forward current	I_{FM}	625	mA
Mean rectifying current	I_O	200	mA
Surge current(1s)	I_{surge}	1000	mA
Power dissipation	P_{tot}	300	mW
Junction temperature	T_j	175	$^\circ C$
Storage temperature	T_s	-65 to +175	$^\circ C$

Characteristics at $T_a = 25^\circ C$

	Symbol	Min.	Typ.	Max.	Unit
Forward voltage at $I_F = 200mA$	V_F	-	-	1.5	V
Reverse current at $V_R = 220V$	I_R	-	-	10	μA
Capacitance between terminals at $f = 1MHz$	C_T	-	-	3	pF
Reverse recovery time at $I_F = 20mA, I_R = 20mA, R_L = 50\Omega$	t_{rr}	-	-	75	ns



®

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